74HC1G02; 74HCT1G02

2-input NOR gate Rev. 04 — 11 July 2007

Product data sheet

General description 1.

74HC1G02 and 74HCT1G02 are high speed Si-gate CMOS devices. They provide a 2-input NOR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC02 and 74HCT02.

2. **Features**

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

Ordering information

Table 1. **Ordering information**

Type number	Package								
	Temperature range	Name	Description	Version					
74HC1G02GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1					
74HCT1G02GW			body width 1.25 mm						
74HC1G02GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74HCT1G02GV									

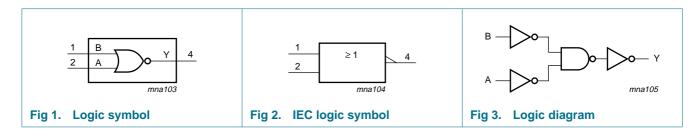
Marking

Table 2. **Marking codes**

Type number	Marking
74HC1G02GW	НВ
74HCT1G02GW	ТВ
74HC1G02GV	H02
74HCT1G02GV	T02

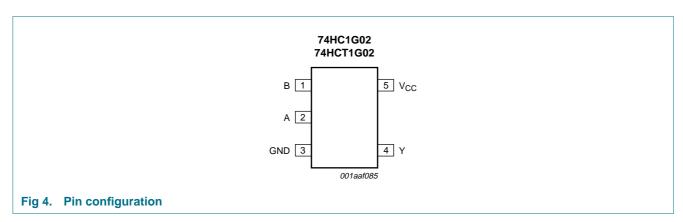


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input
A	2	data input
GND	3	ground (0 V)
Υ	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs	Output	
Α	В	Υ
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G02		74	4HCT1G	02	Unit	
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	V _{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	onditions -40 °C to +85 °C -40 °C to +125		Conditions $-40 ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$ $-40 ^{\circ}\text{C}$ t	–40 °C to +85 °C		-40 °C to +85 °C	o +125 °C	Unit
			Min	Тур	Max	Min	Max			
For type 7	74HC1G02									
V _{IH} HIGH-level input	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	V			
	voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	V		
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	V		
V_{IL}	LOW-level input	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	V		
	voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	V		
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	V		

^[2] Above 55 $^{\circ}$ C the value of P_{tot} derates linearly with 2.5 mW/K.

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max		
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}				1	'		
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V	
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V	
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V	
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V	
		$I_O = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V	
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}							
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V	
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V	
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V	
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V	
		$I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V	
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ	
Cı	input capacitance		-	1.5	-	-	-	pF	
For type	74HCT1G02								
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V	
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	0.8	-	0.8	V	
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}							
	voltage	$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V	
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}							
	voltage	$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V	
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V	
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ	
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A}$	-	-	500	-	850	μΑ	
C _I	input capacitance		-	1.5	-	-	-	pF	

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	
For type	74HC1G02				•			'	
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	8	20	-	23	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[2]	-	18	-	-	-	pF
For type	74HCT1G02								
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	11	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
C _{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	19	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz

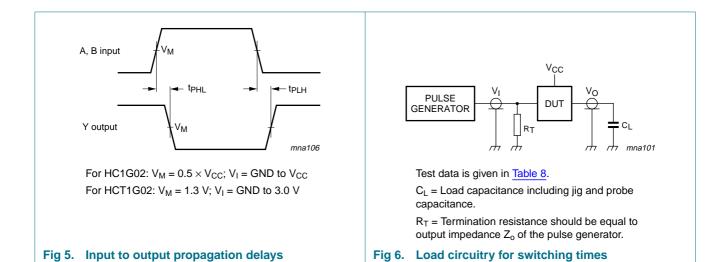
 f_o = output frequency in MHz

C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

12. Waveforms

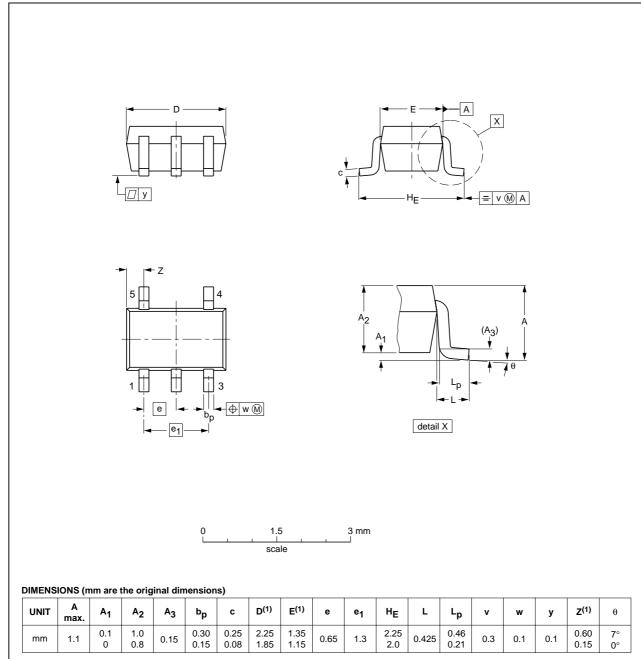


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13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATI	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A		-00-09-01 03-02-19
				1	03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

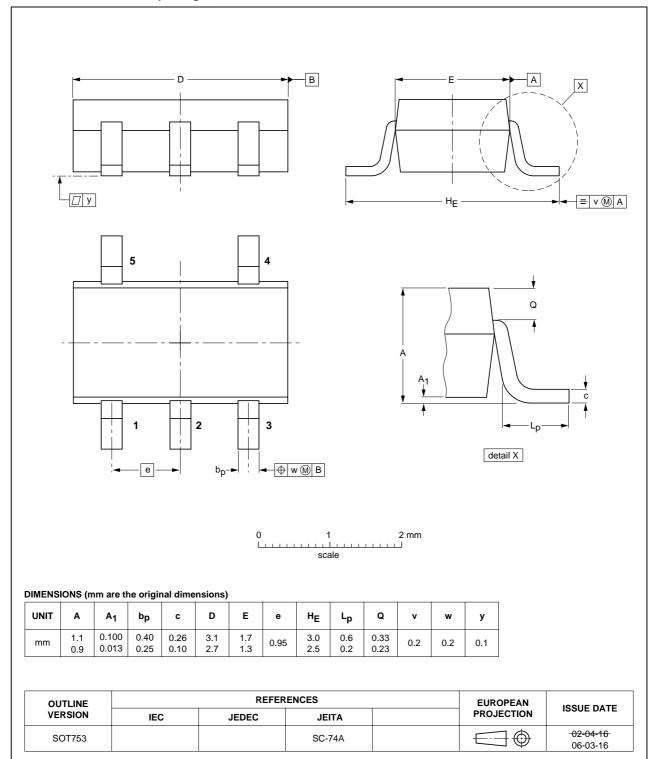


Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

Release date	Data sheet status	Change notice	Supersedes				
20070711	Product data sheet	-	74HC_HCT1G02_3				
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.							
 Legal texts! 	 Legal texts have been adapted to the new company name where appropriate. 						
 Package SC 	OT353 changed to SOT353-	1 in <u>Table 1</u> and <u>Figure</u>	<u>7</u> .				
 Quick refere 	ence data and Soldering sec	tions removed.					
 Section 2 "F 	eatures" updated.						
20020517	Product specification	-	74HC_HCT1G02_2				
20010302	Product specification	-	74HC_HCT1G02_1				
19980831	Product specification	-	-				
	20070711 The formation guidelines of Legal texts Package SO Quick reference Section 2 "Formation 20020517 20010302	 20070711 Product data sheet The format of this data sheet has been guidelines of NXP Semiconductors. Legal texts have been adapted to the network package SOT353 changed to SOT353- Quick reference data and Soldering section 2 "Features" updated. 20020517 Product specification 20010302 Product specification 	Product data sheet The format of this data sheet has been redesigned to comply a guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name whee Package SOT353 changed to SOT353-1 in Table 1 and Figure Quick reference data and Soldering sections removed. Section 2 "Features" updated. 20020517 Product specification - 20010302 Product specification -				

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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NL17SG32P5T5G NL17SG86DFT2G NLU1G32CMUTCG NLV14001UBDR2G NLVVHC1G132DTT1G NLVVHC1G86DTT1G
NLX1G11AMUTCG NLX1G97MUTCG 746427X 74AUP1G17FW5-7 74LS38 74LVC1G08Z-7 74LVC32ADTR2G 74LVC1G125FW4-7
74LVC08ADTR2G MC74HCT20ADTR2G NLV14093BDTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G NLV17SZ126DFT2G
NLV27WZ17DFT2G NLV74HC02ADR2G NLV74HC08ADR2G NLVVHC1GT32DFT1G 74HC32S14-13 74LS133 74LVC1G32Z-7
M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7 M38510/06202BFA NLV74HC08ADTR2G NLV74HC14ADR2G
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